TELEFUNKEN electronic
Creative Technologies

TFK 3070 D

Preliminary specifications

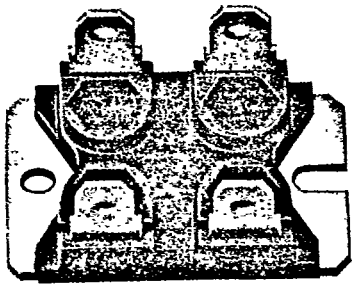
T-33-35

NPN Silicon Darlington Power Transistor

Applications:
- Motor-control (380 V-mains)
- UPS (Uninterruptible power supplies)
- High power SMPS (≧1000 W)
- Battery chargers
- Welding equipments
- Inductive heating equipment

Features:
- High reverse voltage
- Short switching times
- Very fast C-E-free-wheel diode
- Base 1 and base 2 connectable
- Triple diffusion technique
- Glass passivation

Case variations



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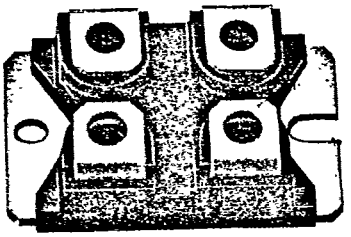

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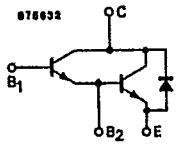
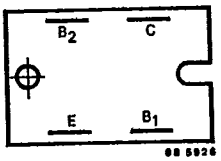
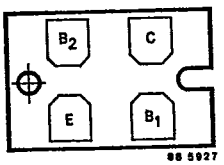
Terminal connections







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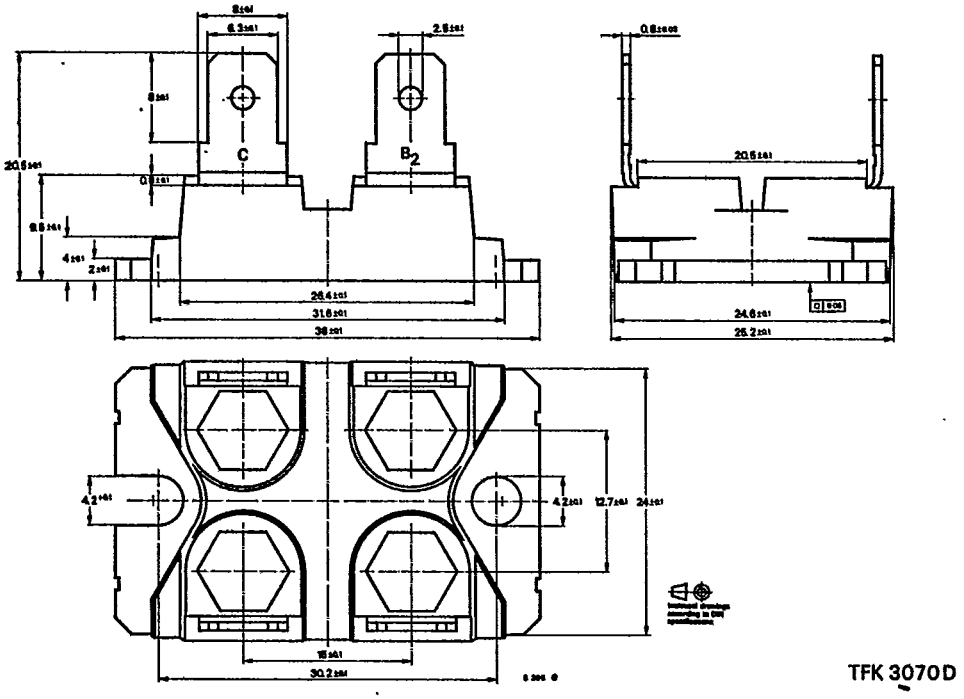
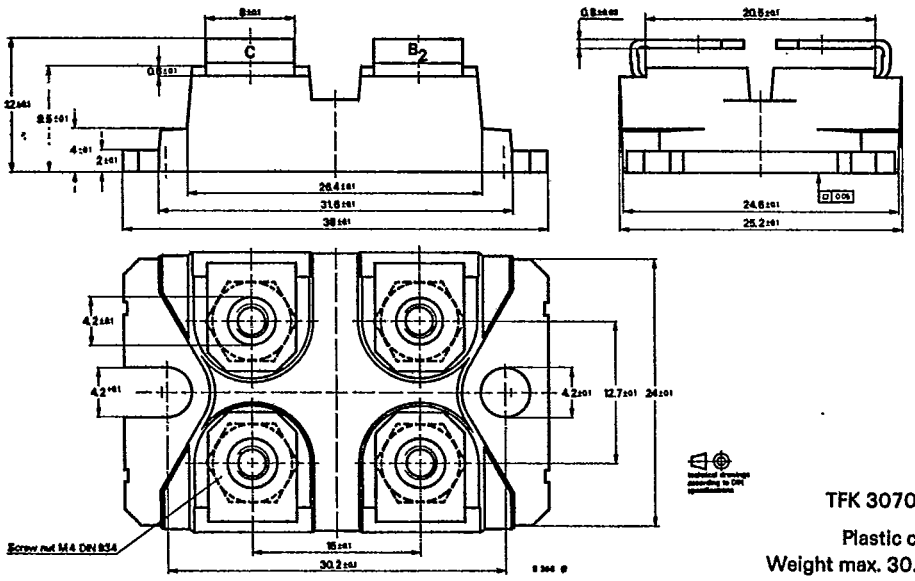
Dimensions in mm



TFK 3070D



TFK 3070DA

Plastic case
Weight max. 30.0 g

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Absolute maximum ratings

Collector-emitter voltage	V_{CEO}	700	V
	V_{CES}	1000	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	20	A
Collector peak current	I_{CM}	30	A
Base current	I_B	4	A
Base peak current	I_{BM}	8	A
Total power dissipation $T_{case} = 25$ °C	P_{tot}	125	W
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−40...+150	°C
Insulation voltage	V_{is}	2500	V

Maximum thermal resistances

Junction case			
Power transistor	R_{thJC}	1.0	K/W
Free-wheel diode	R_{thJC}	2.0	K/W

Characteristics

$T_{case} = 25$ °C, unless otherwise specified

			Min.	Typ.	Max.	
Collector cut-off current						
$V_{CER} = 1000$ V, $R_1 = 270\ \Omega$, $R_2 = 100\ \Omega$		I_{CER}			1.0	mA
$V_{CER} = 1000$ V, $R_1 = 270\ \Omega$, $R_2 = 100\ \Omega$, $T_{case} = 100$ °C		I_{CER}			4.5	mA
Emitter cut-off current						
$V_{EB} = 5$ V	T1, T2	I_{EBO}			1.0	mA
Collector-emitter breakdown voltage						
$I_C = 750$ mA, $L = 125$ mH		$V_{(BR)CEO}$	700			V
$I_C = 1$ mA, $R_1 = 270\ \Omega$, $R_2 = 100\ \Omega$		$V_{(BR)CER}$	1000			V
Emitter-base breakdown voltage						
$I_E = 5$ mA	T1, T2	$V_{(BR)EBO}$	7			V
Collector saturation voltage						
$I_C = 17$ A, $I_B = 1.4$ A		V_{CEsat}		1.4		V
$I_C = 17$ A, $I_B = 1.4$ A, $T_{case} = 125$ °C		V_{CEsat}			2.4	V
Base saturation voltage						
$I_C = 12$ A, $I_B = 0.35$ A		V_{BEsat}		1.85		V
$I_C = 12$ A, $I_B = 0.35$ A, $T_{case} = 125$ °C		V_{BEsat}			3.0	V
DC forward current transfer ratio						
$V_{CE} = 2$ V, $I_C = 12$ A		h_{FE}	35			

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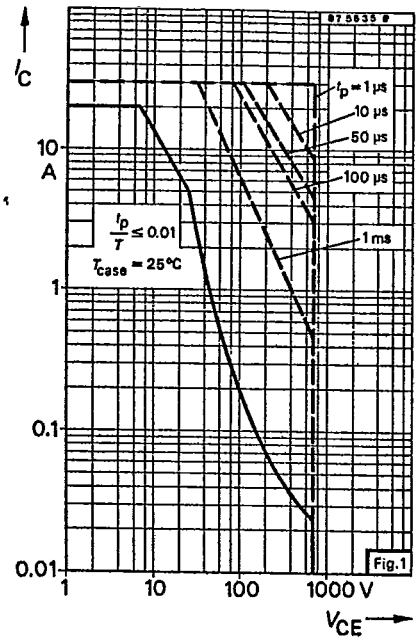
			Min.	Typ.	Max.	
Dynamic saturation voltage $V_S = 300$ V, $R_C = 25\ \Omega$, $I_{B1} = 0.55$ A, $T_{case} = 100$ °C	3 µs 5 µs	$V_{CEsatdyn.}$ $V_{CEsatdyn.}$		16 12	30 20	V V
Collector-emitter working voltage $I_{CWoff} = 15$ A, $I_{B1} = 1.4$ A, $L = 12$ µH $-V_{BB} = 7$ V, $R_{BB} = 0.6\ \Omega$, $V_S = 50$ V		V_{CEW}	700			V
Forward voltage of the diode $I_F = 17$ A, $T_{case} = 100$ °C		V_F			2.0	mA

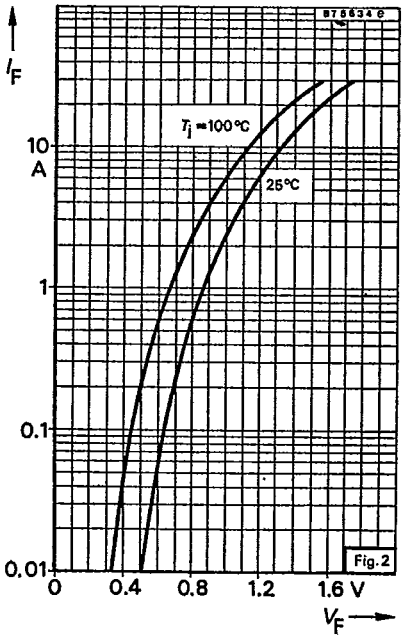
Switching characteristics

Inductive load, $T_{case} = 100$ °C

$I_C = 12$ A, $I_{B1} = 0.35$ A, $L = 0.2$ mH, $V_{clamp} = 700$ V
$-V_{BB} = 7$ V, $R_{BB} = 0.6\ \Omega$, $V_S = 50$ V

Storage time	t_s	4.0	7.0	µs
Fall time	t_f	0.4	0.6	µs
Cross over time	t_c	1.0	1.4	µs





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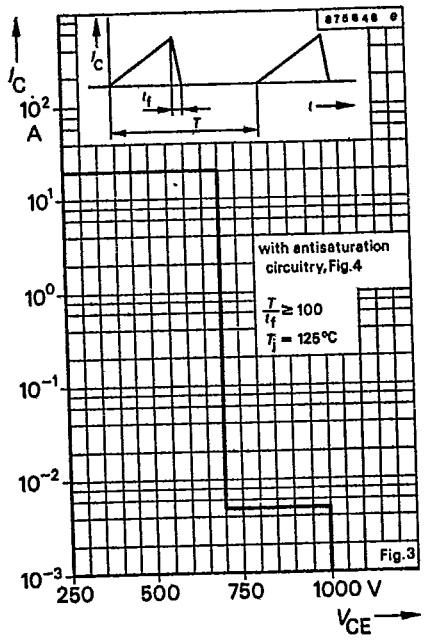


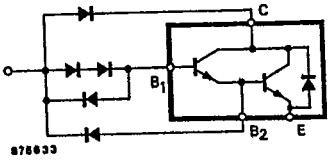
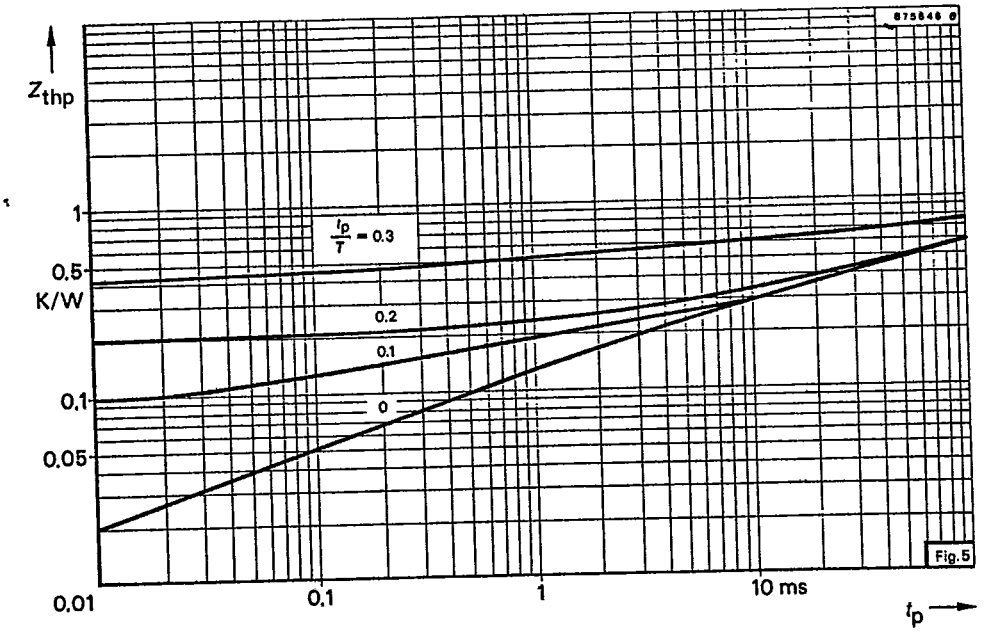


Fig. 4 Antisaturation circuitry



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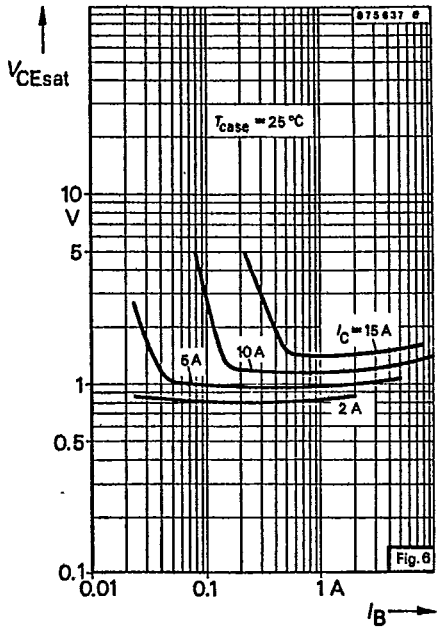


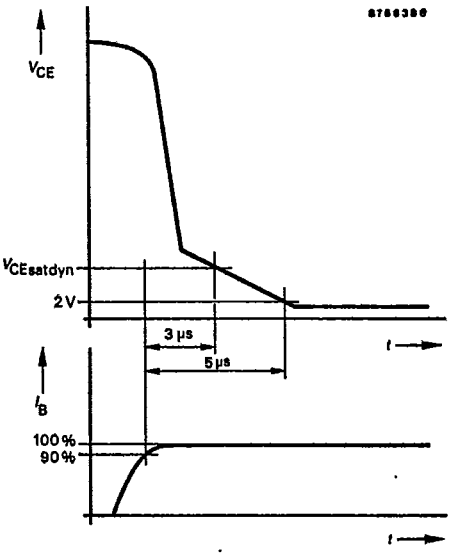
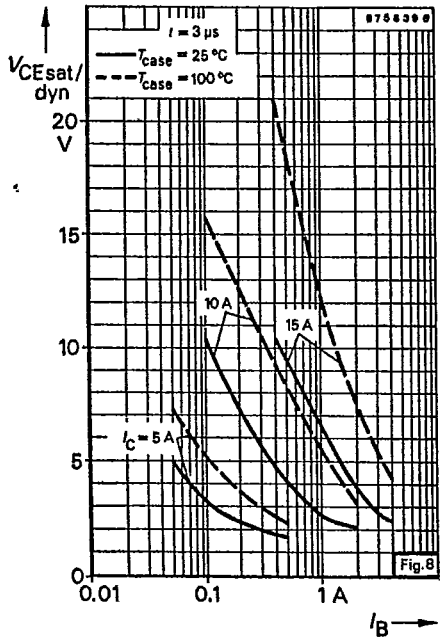
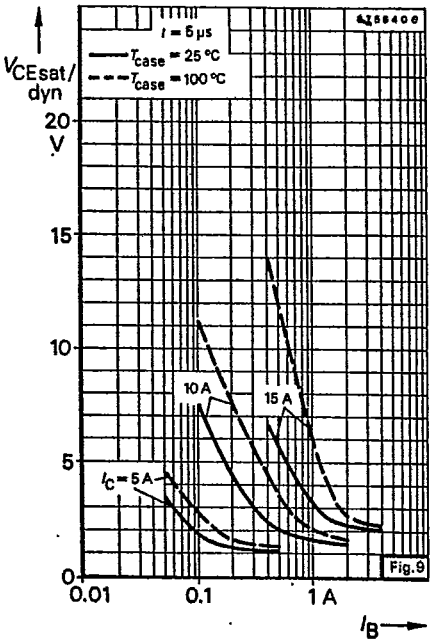
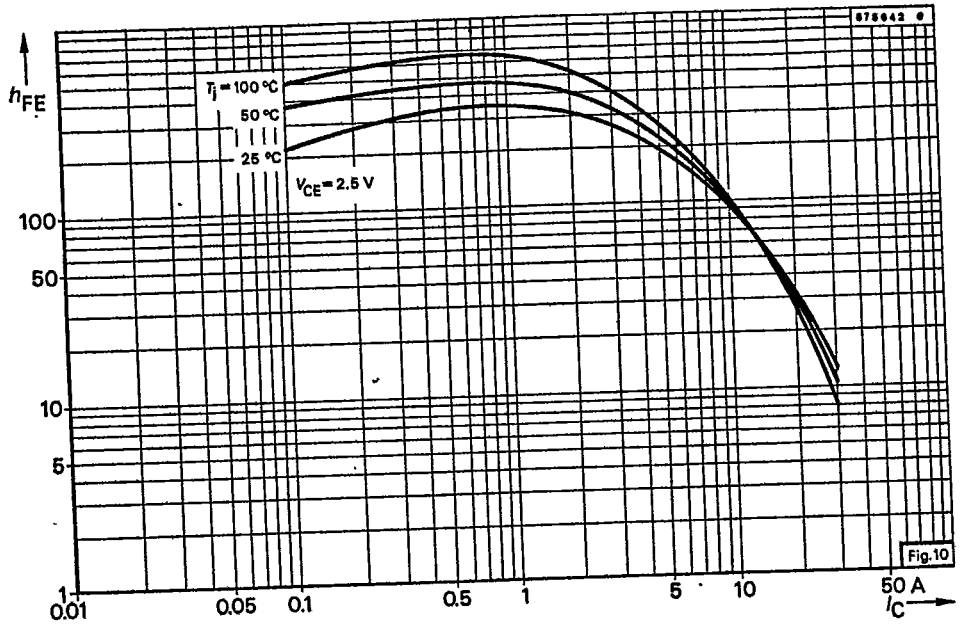
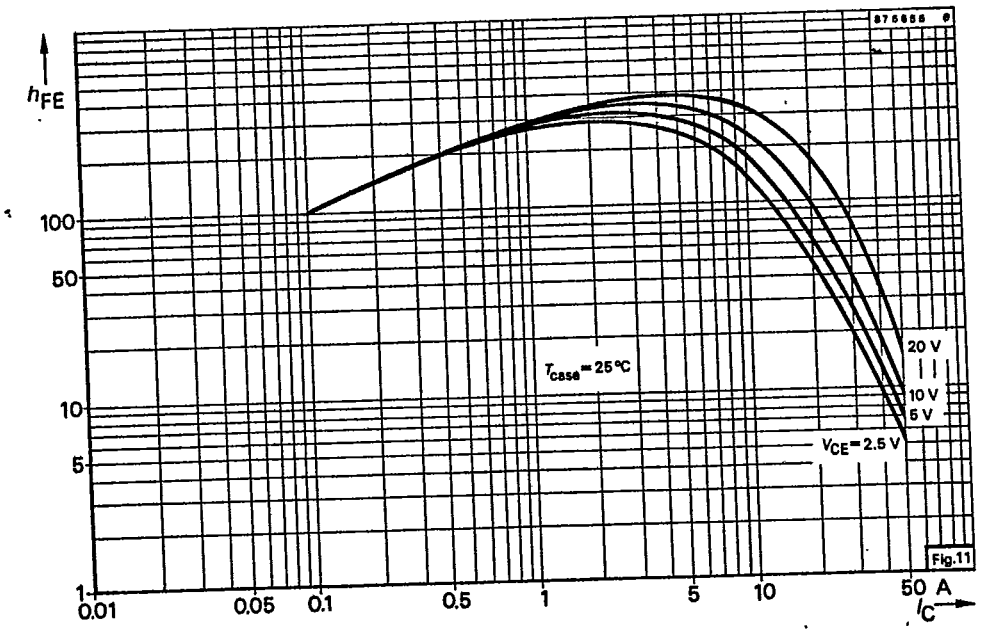


Fig. 7 $V_{CEsatdyn}$-definition






h_{FE}
T_j = 100 °C
50 °C
25 °C
V_{CE} = 2.5 V
100
50
10
5
1
0.01
0.05
0.1
0.5
1
5
10
50 A
I_C
Fig.10


h_{FE}
100
50
10
5
1
T_{case} = 25 °C
20 V
10 V
5 V
V_{CE} = 2.5 V
0.01
0.05
0.1
0.5
1
5
10
50 A
I_C
Fig.11

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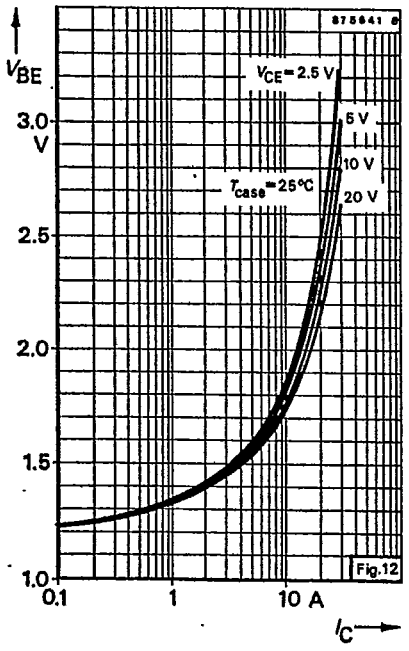

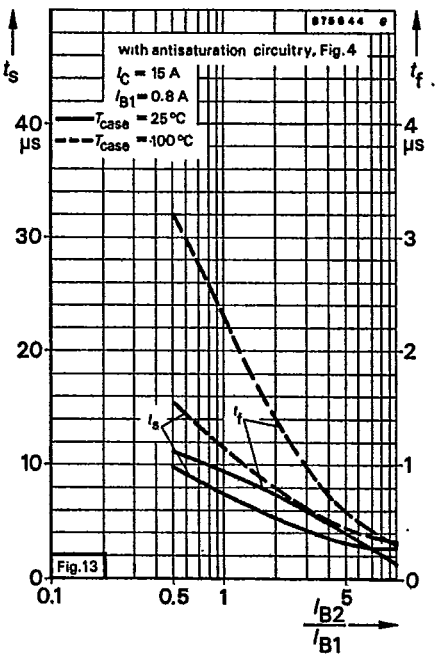

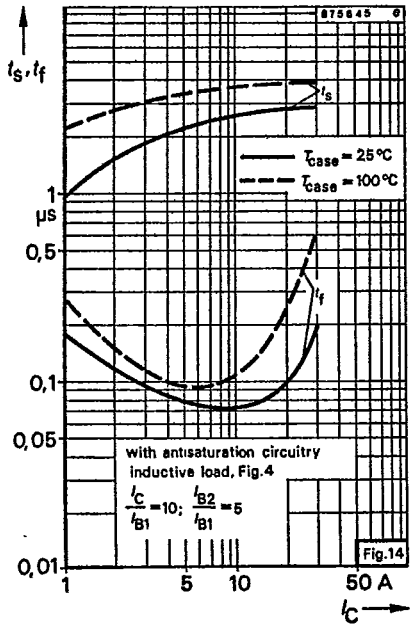

T-91-20

● Family of curves

Besides the static (d. c.) and dynamic (a. c.) characteristics, family of curves are given for specified operating conditions. They show the typical interdepedence of individual characteristics. Partly are given the scattering limits. They signify that at least 95% of the delivery lies inside these tolerances.

6.6. Additional informations

Preliminary specifications

This heading indicates that some information on the device concerned may be subject to slight changes.

Not for new developments

This heading indicates that the device concerned should not be used in equipment under development, it is, however, available for present production.

7. Taping and reeling

7.1. Taping of TO-92 transistors

Standard reeling: Taped on reel, reeled together with a paper film.

7.1.1. Order Numbers

Add the taping-code to the order number.

Example:

BC 238 C DU 06 Z

- Order-No. of Type
- Code for TO-92 Transistors
- Orientation of transistor on tape [1]
- Additional marking for specials [2]

[1] 06 = View on flat side of transistor, view on gummed tape
05 = View on round side of transistor, view on gummed tape

[2] Additional marking "0": Taping without paper film

Additional marking "Z": Zigzag folded tape inspecial box. Marking for orientation of transistor not necessary, because box can be opened on top or botton.

Example for order No.: BC 237 C DU Z

A E G CORP

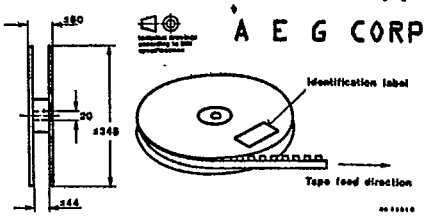

Fig. 7.1. Dimensions of reel in mm

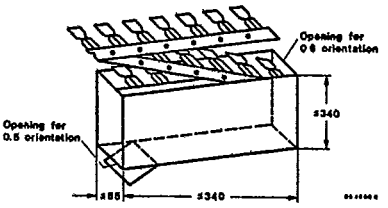

Fig. 7.2. Dimension of box for Zigzag folding in mm

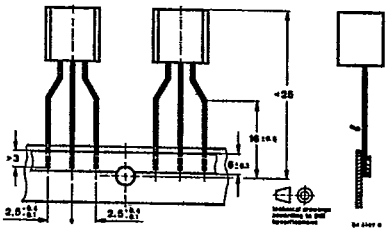

Fig. 7.3. Dimensions of tape in mm

7.1.2 Quantity of devices

1 000 devices per reel

2 000 devices per folded tape in special box.

7.2 Taped transistors in SOT 23 and SOT 143 case

a) Standard taping

Designation is attached with code GS 08 in case of standard taping. Example for normal version transistors as standard taped: BF 569-GS08.

Example for R-version transistors as standard taped: BF 569 R-GS 08.

In case of standard taping, the transistor orientation on the tape is shown in Fig. 7.4 and Fig. 7.5.

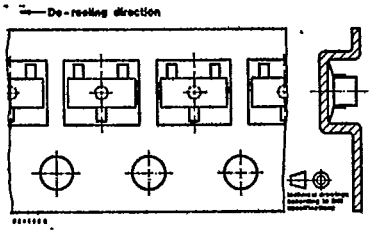

Fig. 7.4 Standard taped SOT 23

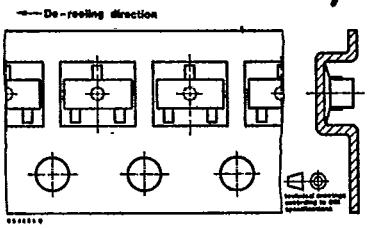

Fig. 7.6 Reverse taped SOT 23

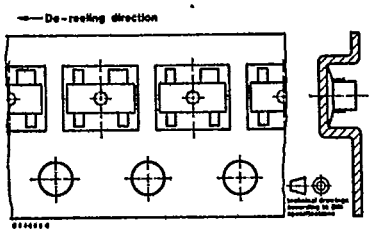

Fig. 7.5 Standard taped SOT 143

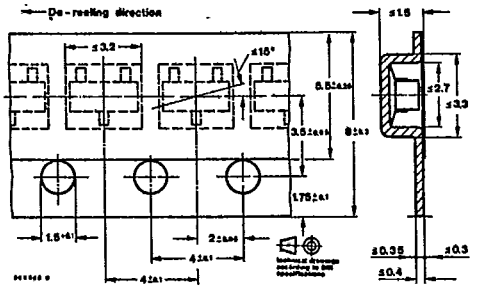

Fig. 7.7 Dimensions of tape in mm

b) Reverse taping
Desigantion is attached with code GS 07 in case of reverse taping. Example for normal version transistors as reverse taped: BF 569 R-GS 07. Example for R-version transistors as reverse taping: BF 569 R-GS 07.

In case of reverse taping, the transistor orientation on the tape is shown in Fig. 6.
Regarding MOF-FET and MES-FET devices, reverse taping is at present not available.

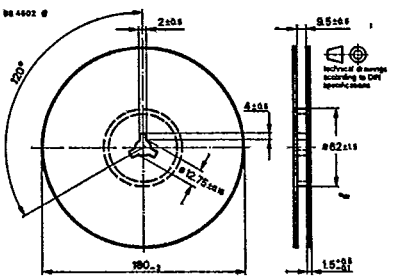

Fig. 7.8 Dimensions of reel in mm

7.2.2 Quantity of devices
3000 devices per reel

8. Assessories

Number	Fig.	Designation	For case
119880	8.1.	Isolating washer thickness 60 µm	12A 3 DIN 41869 JEDEC TO 126 (SOT 32)
564542	8.2.	Isolating washer thickness 50 µm	14A 3 DIN 41869 JEDEC TO 220 (SOT 78)
912884	8.3	Isolating washer thickness 50 µm	15A 3 DIN 41869 (TOP3) for clip mounting
191131	8.4	Isolating washer thickness 50 µm	15A 3 DIN 41869 (TOP3) for screw mounting
191140	8.5	Mounting clip	15A 3 DIN 41869 (TOP3)
569524	8.6	Isolating washer thickness 100 µm + 50 µm	3B 2 DIN 41872 JEDEC TO 3 Devices with high reverse voltage